

30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

93 A

Features

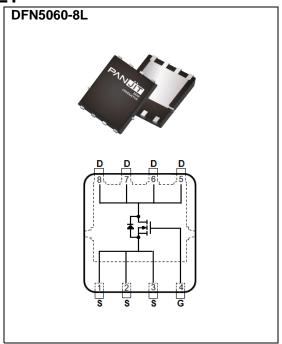
- RDS(ON), VGS@10V, ID@20A<3.6m Ω
- RDS(ON), VGS@4.5V, ID@20A<6.4m Ω
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current ^(Note 3)	T _C =25°C	l _D	93		
	Tc=100°C		66	Α	
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	372		
Power Dissipation	T _C =25°C	Po	50	W	
	Tc=100°C		25		
Continuous Drain Current(Note 4)	T _A =25°C	l _D	24.6		
	T _A =70°C		20.6	A	
Power Dissipation	T _A =25°C	PD	3.3	W	
	T _A =70°C		2.3		
Single Pulse Avalanche Energy ^(Note 5)		Eas	46	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	R _{θJC}	3	°C/W	
	Junction to Ambient	$R_{\theta JA}$	45		



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS} V _{GS} =0V, I _D =250uA		30	-	-	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.3	1.8	2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	-	2.9	3.6	mΩ	
		V _{GS} =4.5V, I _D =20A	-	4.9	6.4		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	
Dynamic ^(Note 6)	•						
Total Gate Charge	Q_g	V _{DS} =24V, I _D =20A,	-	21	-		
Gate-Source Charge	Qgs		-	3.6	-	nC	
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	3.2	-		
Input Capacitance	Ciss	V 05V V 0V	-	1260	-	pF	
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V,	-	560	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	44	-		
Gate resistance	Rg	f=1MHz	-	0.85	-	Ω	
Turn-On Delay Time	td _(on)		-	15	-		
Turn-On Rise Time	tr	V _{DS} =24V, I _D =20A,	-	26	-		
Turn-Off Delay Time	td _(off)	$V_{GS}=10V, R_{G}=3\Omega$	-	24	-	ns	
Turn-Off Fall Time	tf	(Note 2)	-	5	-		
Drain-Source Diode	•						
Diode Forward Current	Is	Tc=25°C	-	-	93	_	
Pulsed Diode Forward Current	I _{SM}	Tc=25 C	-	-	372	А	
Diode Forward Voltage	V _{SD}	Is=20A, V _{GS} =0V	-	0.83	1.1	V	
Reverse Recovery Time	Trr	V _{GS} =0V, I _S =20A	-	31	-	ns	
Reverse Recovery Charge	Qrr	dls/dt=100A/us	-	19	-	nC	

NOTES:

- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an ReJC=3°C/W.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH, I_{AS}=14A, V_{DD}=30V, V_{GS}=10V, Starting T_J=25°C. the chip is about to carry I_{AS}≈27A.
- 6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

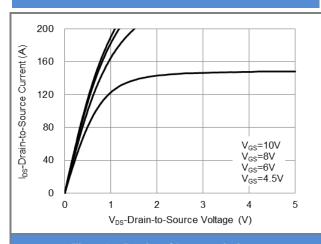


Fig.1 On-Region Characteristics

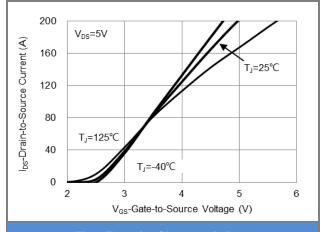


Fig.2 Transfer Characteristics

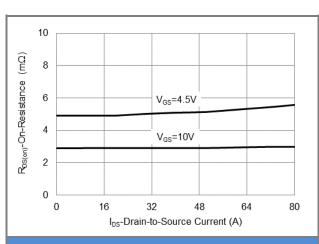


Fig.3 On-Resistance vs. Drain Current

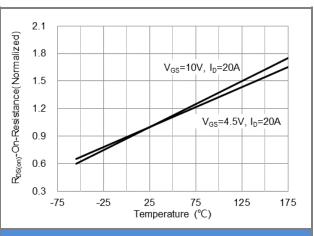


Fig.4 On-Resistance vs. Junction temperature

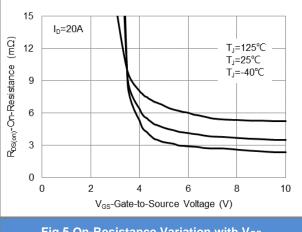


Fig.5 On-Resistance Variation with V_{GS}

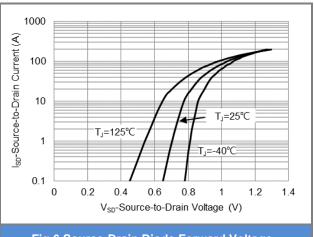


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

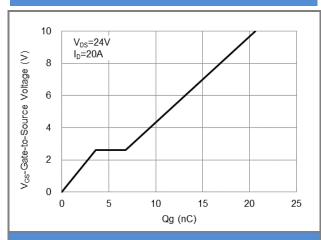


Fig.7 Gate-Charge Characteristics

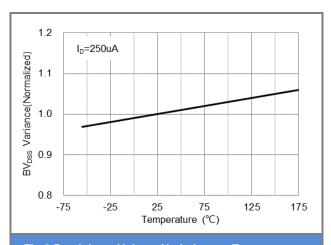


Fig.8 Breakdown Voltage Variation vs. Temperature

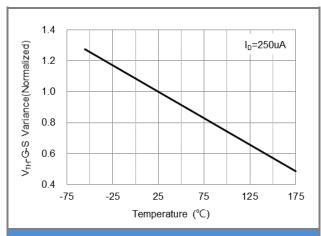


Fig.9 Threshold Voltage Variation with Temperature

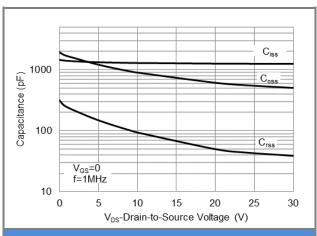
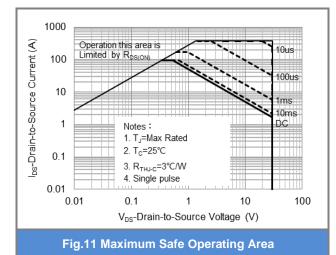
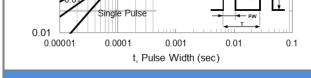


Fig.10 Capacitance vs. Drain-Source Voltage

D=0.5

0.0





 $T_{J,PK}=T_C+P_{DM}*Z_{TH-JC}*R_{TH-JC}$

R_{TH-JC}=3°C/W

T_C=25°C

Fig.12 Normalized Transient Thermal Impedance

Transient Thermal Impedance(Normalized)

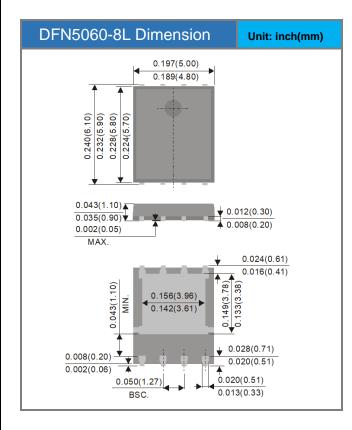
0.1

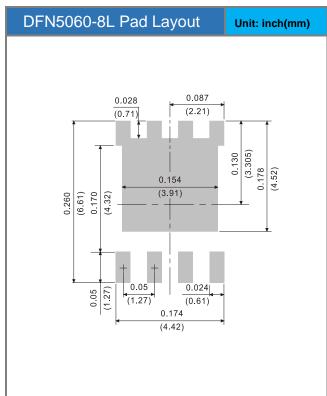


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ5524-AU	DFN5060-8L	3K pcs / 13" reel	Q5524	

Packaging Information & Mounting Pad Layout





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